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What is claimed is:

- 1 1. A method of measuring a pattern comprising:
2 exposing an evaluation pattern having at least two
3 light-impermeable line patterns to form on a target a plurality
4 of transferred patterns each based on said evaluation pattern;
5 and
6 detecting which one or ones among said transferred patterns
7 is brought into a state that any one of said two light-impermeable
8 line patterns disappears.
- 1 2. The method as claimed in Claim 1, wherein a plurality of
2 said evaluation patterns are provided on a single mask, and said
3 exposing is executed with said single mask to thereby form said
4 plurality of transferred patterns on said object.
- 1 3. The method as claimed in Claim 2, wherein at least one
2 of said light-impermeable line patterns is different from one
3 another among said evaluation patterns.
- 1 4. The method as claimed in Claim 3, wherein each of said
2 evaluation patterns has at least one additional
3 light-impermeable line pattern between said two
4 light-impermeable line patterns, and in at least one of said
5 evaluation patterns, each of said two light-impermeable line
6 patterns is different in width from said additional
7 light-impermeable line pattern.
- 1 5. The method as claimed in Claim 3, wherein said plurality

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1 9. A method for measuring a coma aberration in an optical
2 system with a projection optical system, the method comprising:
3 illuminating with light a mask that is provided with a
4 evaluation pattern having at least two light-impermeable line
5 patterns;
6 leading the light through said mask to said projection
7 optical system and exposing a target with an output from said
8 projection optical system to create on said target a plurality
9 of transferred patterns each based on said evaluation pattern;
10 detecting which one or ones among said transferred patterns

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11 is brought into state that any one of said two light-impermeable
12 line patterns disappears; and
13 evaluating a coma aberration in said projection optical
14 system according to a result of said detecting.

1 10. The method as claimed in Claim 9, wherein a plurality of
2 said evaluation patterns are provided on said mask and said
3 exposing is executed with said mask to form said plurality of
4 transferred patterns on said target, and at least one of said
5 light-impermeable lines is different from one another among said
6 evaluation patterns.

1 11. The method as claimed in Claim 10, further comprising:
2 determining a correlation between magnitude of coma
3 aberration belonging to said projection optical system and the
4 line widths of a state where one of said two light-impermeable
5 line patterns disappears,
6 wherein the magnitude of coma aberration is determined
7 from said correlation and said result of detection.

1 12. The method as claimed in Claim 9, wherein a plurality of
2 transferred patterns are formed on said target by executing said
3 exposing a plurality of times with said mask while varying
4 exposure amount for each exposure.

1 13. The method as claimed in Claim 12, further comprising:
2 determining a correlation between magnitude of coma
3 aberration belonging to said projection optical system and the

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4 light exposures of a state where any one of said two
5 light-impermeable line patterns disappears,
6 wherein the magnitude of coma aberration is determined
7 from said correlation and said result of detection.

1 14. A coma aberration measuring method comprising:
2 placing an evaluation mask on a mask stage of a projection
3 exposure device;
4 placing an evaluation wafer with a photosensitive film
5 coated on its surface on a wafer stage;
6 illuminating, with a lighting optical system, said
7 evaluation mask that is provided with an evaluation pattern
8 having at least two line patterns, focusing an image of said
9 evaluation pattern on said evaluation mask onto the surface of
10 said evaluation wafer by means of a projection optical system
11 and exposing it to light;
12 developing an exposed photosensitive film to form a
13 plurality of transferred patterns on said photosensitive film
14 each based on said evaluation patterns;
15 distinguishing among said plurality of transferred
16 patterns, between ones having all said line patterns and ones
17 not having; and
18 determining magnitude of coma aberration from the result
19 of such distinction.

1 15. The coma aberration measuring method as claimed in Claim
2 14, wherein a plurality of said evaluation patterns are provided
3 on said evaluation mask and at least one of said line patterns

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4 is different from one another among said evaluation patterns.

1 16. The coma aberration measuring method as claimed in Claim
2 15, wherein in each of said evaluation patterns, at least two
3 said line patterns are formed as a line portion between a pair
4 of reference lines; and

5 wherein in each of said transferred patterns, a relative
6 positional deviation in a direction of line alignment of a center
7 position of said line portion from a center position of said
8 reference line pair is measured and the magnitude of coma
9 aberration is determined based on said relative positional
10 deviation.

1 17. The coma aberration measuring method as claimed in Claim
2 14, wherein a plurality of transferred patterns are formed by
3 executing said exposing a plurality of times with said evaluation
4 mask while varying exposure amount for each exposure.

1 18. The coma aberration measuring method as claimed in Claim
2 17, wherein in said evaluation pattern, at least two said line
3 patterns are formed as a line portion between a pair of reference
4 lines;

5 wherein in each of said transferred patterns a relative
6 positional deviation in a direction of line alignment of a center
7 position of said line portion from a center position of said
8 reference line pair is observed; and

9 wherein the light exposure used for a transferred pattern
10 in which that relative positional deviation becomes substantial

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11 is regarded as a critical exposure and the coma aberration which
12 corresponds to this critical exposure is defined as the coma
13 aberration for said optical system.

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